



Product data sheet

1. Product profile

1.1 General description

Silicon Monolithic Microwave Integrated Circuit (MMIC) wideband amplifier with internal matching circuit in a 6-pin SOT363 plastic SMD package.

1.2 Features and benefits

- Internally matched to 50 Ω
- A gain of 22.2 dB at 250 MHz increasing to 23.0 dB at 2150 MHz
- Output power at 1 dB gain compression = 2 dBm
- Supply current = 14.3 mA at a supply voltage of 3.3 V
- Reverse isolation > 29 dB up to 2 GHz
- Good linearity with low second order and third order products
- Noise figure = 4 dB at 950 MHz

1.3 Applications

- LNB IF amplifiers
- General purpose low noise wideband amplifier for frequencies between DC and 2.2 GHz

2. Pinning information

Pin	Description	Simplified outline	Graphic symbol
1	V _{CC}		
2, 5	GND2		
3	RF_OUT		6-
4	GND1		
6	RF_IN		4 2, 5 777 77 sym052

3. Ordering information

Table 2. Ordering information

Type number	Package		
	Name	Description	Version
BGA2801	-	plastic surface-mounted package; 6 leads	SOT363



4. Marking

Table 3. Marking]	
Type number	Marking code	Description
BGA2801	*E8	* = - : made in Hong Kong
		* = p : made in Hong Kong
		* = W : made in China
		* = t : made in Malaysia

5. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage	RF input AC coupled	-0.5	+5.0	V
I _{CC}	supply current		-	55	mA
P _{tot}	total power dissipation	T _{sp} = 90 °C	-	200	mW
T _{stg}	storage temperature		-40	+125	°C
Tj	junction temperature		-	125	°C
P _{drive}	drive power		-	+10	dBm

6. Thermal characteristics

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Тур	Unit		
R _{th(j-sp)}	thermal resistance from junction to solder point	P_{tot} = 200 mW; T_{sp} = 90 °C	300	K/W		

7. Characteristics

Table 6.Characteristics

 $V_{CC} = 3.3 \text{ V}; Z_S = Z_L = 50 \Omega; P_i = -30 \text{ dBm}; T_{amb} = 25 \text{ °C}; \text{ measured on demo board; unless otherwise specified.}$

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CC}	supply voltage		3.0	3.3	3.6	V
I _{CC}	supply current		12.2	14.3	16.3	mA
G _p	power gain	f = 250 MHz	21.6	22.2	22.8	dB
		f = 950 MHz	21.7	22.4	23.1	dB
		f = 2150 MHz	21.5	23.0	24.4	dB
RL _{in}	input return loss	f = 250 MHz	15	17	19	dB
		f = 950 MHz	15	17	19	dB
		f = 2150 MHz	10	12	19	dB
RL _{out}	output return loss	f = 250 MHz	13	17	22	dB
		f = 950 MHz	14	15	16	dB
		f = 2150 MHz	10	12	15	dB
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
ISL	isolation	f = 250 MHz	58	78	99	dB
		f = 950 MHz	46	47	49	dB
		f = 2150 MHz	29	32	34	dB
NF	noise figure	f = 250 MHz	3.4	3.8	4.3	dB
		f = 950 MHz	3.4	3.8	4.3	dB
		f = 2150 MHz	3.5	3.9	4.4	dB
B _{-3dB}	-3 dB bandwidth	3 dB below gain at 1 GHz	2.5	2.8	3.1	GHz
K	Rollett stability factor	f = 250 MHz	252	308	363	
		f = 950 MHz	7	8	10	
		f = 2150 MHz	0.7	1.3	1.9	
P _{L(sat)}	saturated output power	f = 250 MHz	4	4	5	dBm
		f = 950 MHz	2	4	5	dBm
		f = 2150 MHz	1	2	3	dBm
P _{L(1dB)}	output power at 1 dB gain compression	f = 250 MHz	1	2	3	dBm
		f = 950 MHz	0	2	3	dBm
		f = 2150 MHz	-1	0	+1	dBm
IP3 _I	input third-order intercept point	$P_{drive} = -34 \text{ dBm}$ (for each tone)				
		f ₁ = 250 MHz; f ₂ = 251 MHz	-10	-8	-6	dBm
		f ₁ = 950 MHz; f ₂ = 951 MHz	-11	-8	-6	dBm
		f ₁ = 2150 MHz; f ₂ = 2151 MHz	-17	-14	-10	dBm
IP3 ₀	output third-order intercept point	$P_{drive} = -34 \text{ dBm}$ (for each tone)				
		f ₁ = 250 MHz; f ₂ = 251 MHz	12	14	16	dBm
		f ₁ = 950 MHz; f ₂ = 951 MHz	12	14	16	dBm
		f ₁ = 2150 MHz; f ₂ = 2151 MHz	6	9	13	dBm
P _{L(2H)}	second harmonic output power	P _{drive} = -31 dBm				
		f _{1H} = 250 MHz; f _{2H} = 500 MHz	-62	-60	-58	dBm
		f _{1H} = 950 MHz; f _{2H} = 1900 MHz	-51	-50	-48	dBm
∆IM2	second-order intermodulation distance	P _{drive} = -34 dBm (for each tone)				
		f ₁ = 250 MHz; f ₂ = 251 MHz	34	45	56	dBc
		f ₁ = 950 MHz; f ₂ = 951 MHz	27	39	50	dBc

Table 6. Characteristics ...continued 1/1 0.01/17 7 50.01 0.1 20.01

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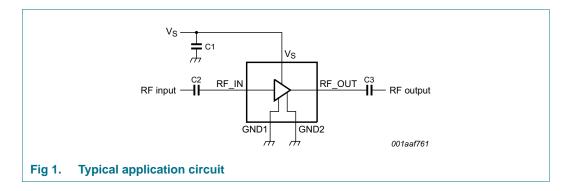
Application information 8.

Figure 1 shows a typical application circuit for the BGA2801 MMIC. The device is internally matched to 50 Ω , and therefore does not need any external matching. The value of the input and output DC blocking capacitors C2 and C3 should not be more than 100 pF for applications above 100 MHz. However, when the device is operated below 100 MHz, the capacitor value should be increased.

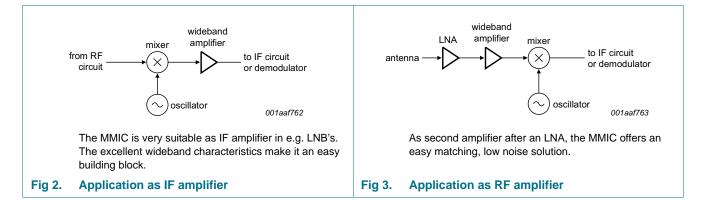
The 22 nF supply decoupling capacitor C1 should be located as close as possible to the MMIC.

BGA2801

The PCB top ground plane, connected to pins 2, 4 and 5 must be as close as possible to the MMIC, preferably also below the MMIC. When using via holes, use multiple via holes as close as possible to the MMIC.



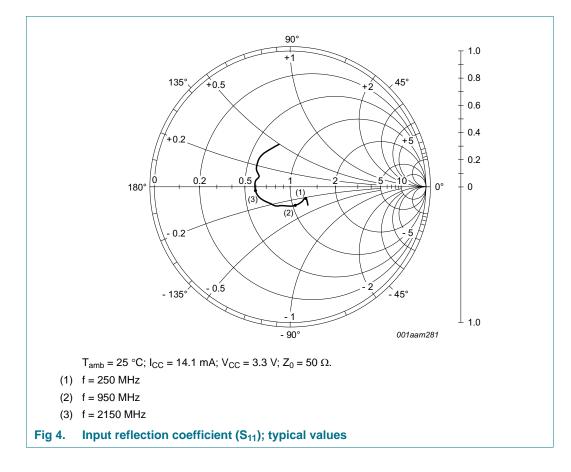
8.1 Application examples



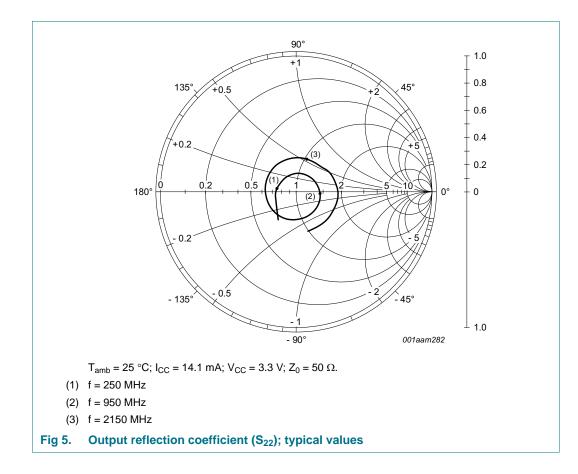
BGA2801

BGA2801 MMIC wideband amplifier

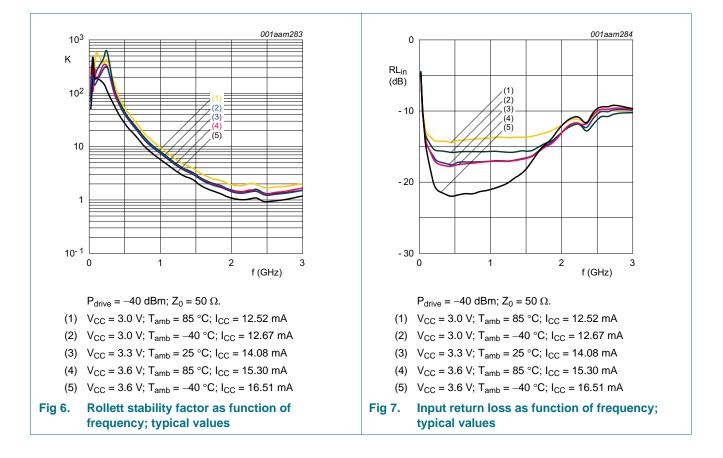
8.2 Graphs



MMIC wideband amplifier

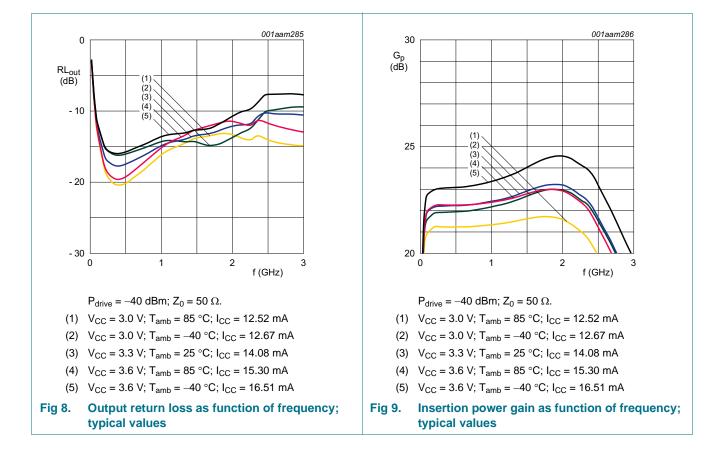


MMIC wideband amplifier



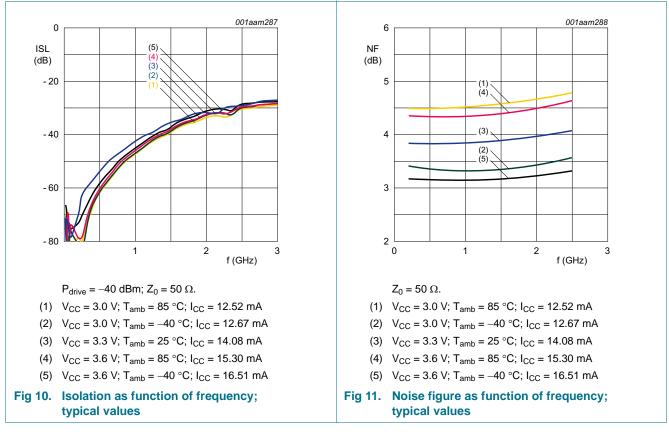
BGA2801

MMIC wideband amplifier



BGA2801

MMIC wideband amplifier



8.3 Tables

Table 7.Supply current over temperature and supply voltagesTypical values.

Symbol	Parameter	Conditions	T _{amb} (°0	T _{amb} (°C)			
			-40	+25	+85		
I _{CC} supply current	supply current	$V_{CC} = 3.0 V$	12.67	12.24	12.52	mA	
		$V_{CC} = 3.3 V$	14.85	14.08	14.27	mA	
		$V_{CC} = 3.6 V$	16.51	15.65	15.30	mA	

Table 8.Second harmonic output power over temperature and supply voltagesTypical values.

Symbol	Parameter	Conditions	Tamb	(°C)		Unit
			-40	+25	+85	
P _{L(2H)}	second harmonic output power	f = 250 MHz; P_{drive} = -33 dBm				
		$V_{CC} = 3.0 V$	-53	-58	-59	dBm
		$V_{CC} = 3.3 V$	-56	-60	-59	dBm
		$V_{CC} = 3.6 V$	-58	-60	-59	dBm
		f = 950 MHz; P_{drive} = -33 dBm				
		V _{CC} = 3.0 V	-46	-50	-54	dBm
		V _{CC} = 3.3 V	-47	-50	-53	dBm
		V _{CC} = 3.6 V	-47	-49	-52	dBm

BGA2801

Symbol	Parameter	Conditions	T _{amb}	(°C)		Unit
			-40	+25	+85	
P _{i(1dB)}	input power at 1 dB gain compression	f = 250 MHz				
		$V_{CC} = 3.0 V$	-20	-20	-20	dBm
		$V_{CC} = 3.3 V$	-20	-19	-19	dBm
		V _{CC} = 3.6 V	-19	-19	-19	dBm
		f = 950 MHz				
		$V_{CC} = 3.0 V$	-20	-20	-20	dBm
		$V_{CC} = 3.3 V$	-20	-20	-20	dBm
		V _{CC} = 3.6 V	-19	-19	-19	dBm
		f = 2150 MHz				
		$V_{CC} = 3.0 V$	-22	-22	-22	dBm
		$V_{CC} = 3.3 V$	-21	-21	-22	dBm
		V _{CC} = 3.6 V	-21	-21	-22	dBm

Table 9. Input power at 1 dB gain compression over temperature and supply voltages *Typical values.*

Table 10. Output power at 1 dB gain compression over temperature and supply voltages Typical values. Values.

Symbol	Parameter	Conditions	Tamb	(°C)		Unit
			-40	+25	+85	
P _{L(1dB)}	output power at 1 dB gain compression	f = 250 MHz				
		$V_{CC} = 3.0 V$	1	1	0	dBm
		$V_{CC} = 3.3 V$	2	2	1	dBm
		$V_{CC} = 3.6 V$	3	3	2	dBm
		f = 950 MHz				
		$V_{CC} = 3.0 V$	1	0	0	dBm
		$V_{CC} = 3.3 V$	2	2	1	dBm
		$V_{CC} = 3.6 V$	3	3	2	dBm
		f = 2150 MHz				
		$V_{CC} = 3.0 V$	0	-1	-2	dBm
		V _{CC} = 3.3 V	1	0	-1	dBm
		V _{CC} = 3.6 V	2	1	0	dBm

MMIC wideband amplifier

Symbol	Parameter	Conditions	T _{amb}	(°C)		Unit
			-40	+25	+85	
P _{L(sat)}	saturated output power	f = 250 MHz				
		$V_{CC} = 3.0 V$	3	3	3	dBm
		V _{CC} = 3.3 V	4	4	4	dBm
		V _{CC} = 3.6 V	5	5	5	dBm
		f = 950 MHz				
		V _{CC} = 3.0 V	3	3	2	dBm
		V _{CC} = 3.3 V	4	4	3	dBm
		$V_{CC} = 3.6 V$	5	5	4	dBm
		f = 2150 MHz				
		$V_{CC} = 3.0 V$	2	1	0	dBm
		$V_{CC} = 3.3 V$	3	2	1	dBm
		V _{CC} = 3.6 V	4	3	1	dBm

Table 11. Saturated output power over temperature and supply voltages Typical values. Values.

Table 12. Second-order intermodulation distance over temperature and supply voltages Typical values. Values.

Symbol	Parameter	Conditions	T _{amb} (°C)			Unit
			-40	+25	+85	
∆IM2 sec	second-order intermodulation distance	$f_1 = 250 \text{ MHz};$ $f_2 = 251 \text{ MHz};$ $P_{drive} = -36 \text{ dBm}$				
		$V_{CC} = 3.0 V$	48	48	42	dBc
		$V_{CC} = 3.3 V$	52	45	41	dBc
		V _{CC} = 3.6 V	49	44	41	dBc
		f ₁ = 950 MHz; f ₂ = 951 MHz; P _{drive} = -36 dBm				
		$V_{CC} = 3.0 V$	38	38	36	dBc
		V _{CC} = 3.3 V	40	39	37	dBc
		V _{CC} = 3.6 V	41	39	37	dBc

MMIC wideband amplifier

Symbol	Parameter	Conditions	T _{amb}	T _{amb} (°C)		
			-40	+25	+85	_
IP3 ₀	output third-order intercept point	$f_1 = 250 \text{ MHz};$ $f_2 = 251 \text{ MHz};$ $P_{drive} = -36 \text{ dBm}$				
		V _{CC} = 3.0 V	13	13	12	dBm
		V _{CC} = 3.3 V	15	14	14	dBm
		V _{CC} = 3.6 V	16	15	14	dBm
		$f_1 = 950 \text{ MHz};$ $f_2 = 951 \text{ MHz};$ $P_{drive} = -36 \text{ dBm}$				
		V _{CC} = 3.0 V	13	12	12	dBm
		V _{CC} = 3.3 V	15	14	13	dBm
		V _{CC} = 3.6 V	16	15	14	dBm
		$f_1 = 2150 \text{ MHz};$ $f_2 = 2151 \text{ MHz};$ $P_{drive} = -36 \text{ dBm}$				
		V _{CC} = 3.0 V	9	8	7	dBm
		V _{CC} = 3.3 V	11	9	8	dBm
		V _{CC} = 3.6 V	12	10	8	dBm

Table 13. Output third-order intercept point over temperature and supply voltages Typical values. Values.

Table 14. -3 dB bandwidth over temperature and supply voltages Typical values.

Symbol	Parameter	Conditions	T _{amb} (°C)			Unit
			-40	+25	+85	
B _{-3dB}	-3 dB bandwidth	$V_{CC} = 3.0 V$	2.875	2.832	2.745	GHz
		$V_{CC} = 3.3 V$	2.902	2.849	2.763	GHz
		$V_{CC} = 3.6 V$	2.920	2.866	2.775	GHz

BGA2801 MMIC wideband amplifier

Test information 9.

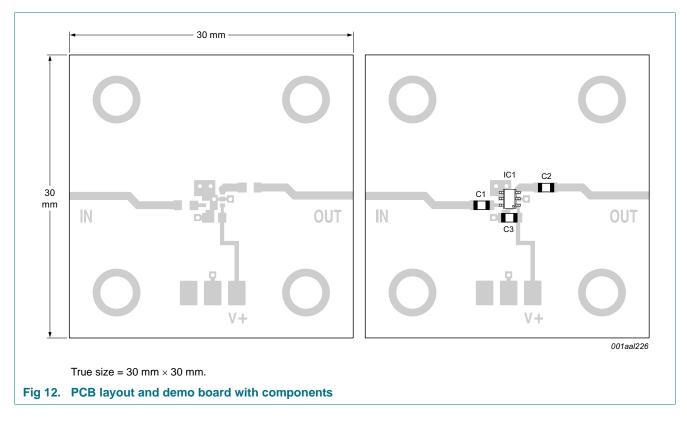


Table 15. List of components used for the typical application

Component	Description	Value	Dimensions
C1, C2	multilayer ceramic chip capacitor	100 pF	0603
C3	multilayer ceramic chip capacitor	22 nF	0603
IC1	BGA2801 MMIC		SOT363

BGA2801

10. Package outline

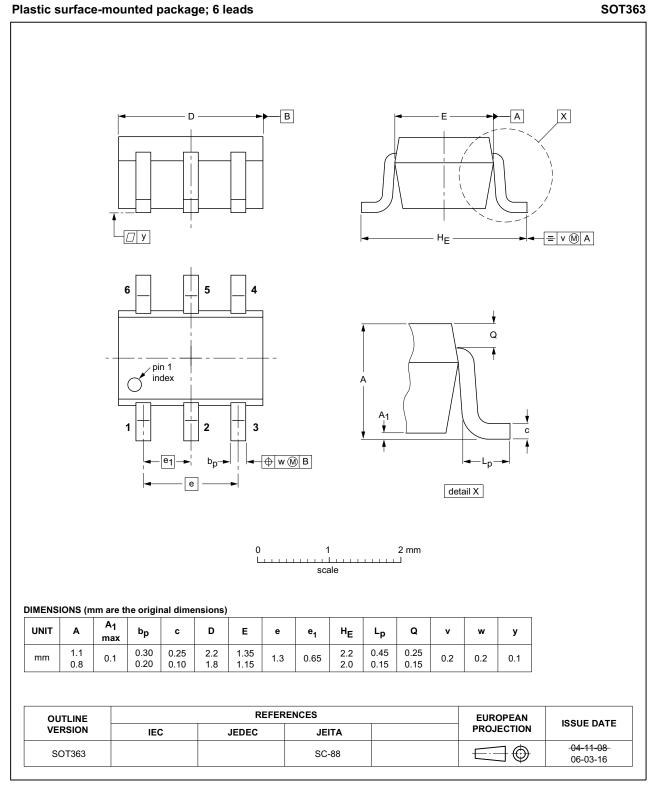


Fig 13. Package outline SOT363

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11. Abbreviations

Table 16. Abbreviations				
Acronym	Description			
DC	Direct Current			
IF	Intermediate Frequency			
LNA	Low-Noise Amplifier			
LNB	Low-Noise Block converter			
PCB	Printed-Circuit Board			
RF	Radio Frequency			
SMD	Surface Mounted Device			

12. Revision history

Table 17. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BGA2801 v.5	20150713	Product data sheet	-	BGA2801 v.4	
Modifications:	of NXP Semic	conductors.	to the new company name where appropriate.		
BGA2801 v.4	20141209	Product data sheet		BGA2801 v.3	
BGA2801 v.3	20120419	Product data sheet	-	BGA2801 v.2	
BGA2801 v.2	20101029	Product data sheet	-	BGA2801 v.1	
BGA2801 v.1	20100817	Product data sheet	-	-	

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Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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15. Contents

1	Product profile 1
1.1	General description 1
1.2	Features and benefits 1
1.3	Applications 1
2	Pinning information 1
3	Ordering information 1
4	Marking 2
5	Limiting values 2
6	Thermal characteristics 2
7	Characteristics 2
8	Application information 3
8.1	Application examples 4
8.2	Graphs 5
8.3	Tables
9	Test information 13
10	Package outline 14
11	Abbreviations 15
12	Revision history 15
13	Legal information 16
13.1	Data sheet status 16
13.2	Definitions
13.3	Disclaimers
13.4	Trademarks 17
14	Contact information 17
15	Contents 18

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